SiO2 Films, Grown using Unaxis ICP Tool with100% SiH4 as well as PECVD Tool, Characterizations						
	Low-Deposition-Rate (SiH_4/O_2/Ar=7.5/15/20 sccm)			High-Deposition-Rate (SiH_4/O_2/Ar=27.5/55/20 sccm)		
	100 °C (ICP)	250 °C (ICP)	250 °C (PECVD)	100 °C (ICP)	250 °C (ICP)	250 °C (PECVD)
Refractive Index	1.45	1.48	1.46	1.47	1.46	1.46
Deposition Rate (nm/min)	40.8	35.9	~40	113.4	114.3	~40
Buffered HF Etch Rate (nm/min)	179	180	520	190	158	520
Stress, MPa (~200 nm film on Si substrate)	-156	-232	-330	-286	-344	-330